

2SC1573, 2SC1573A, 2SC1573B

Silicon NPN triple diffusion planar type

For high breakdown voltage general amplification

For small TV video output

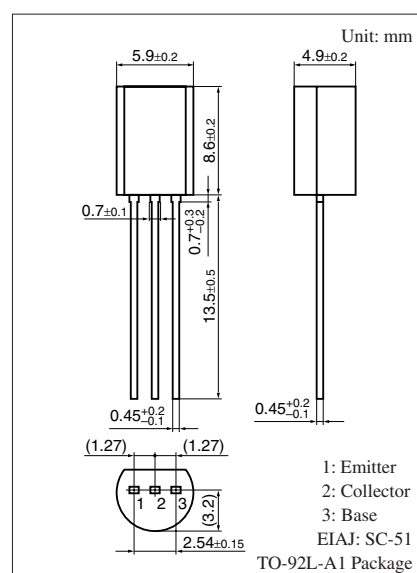
Complementary to 2SC1573 and 2SA0879

■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- High transition frequency f_T

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SC1573	V_{CBO}	250	V
	2SC1573A		300	
	2SC1573B		400	
Collector-emitter voltage (Base open)	2SC1573	V_{CEO}	200	V
	2SC1573A		300	
	2SC1573B		400	
Emitter-base voltage (Collector open)	2SC1573	V_{EBO}	5	V
	2SC1573A		7	
	2SC1573B			
Collector current		I_C	70	mA
Peak collector current		I_{CP}	100	mA
Collector power dissipation		P_C	1	W
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C



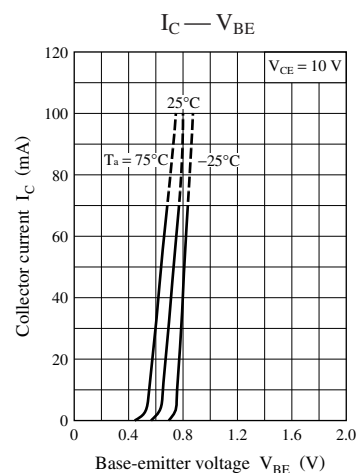
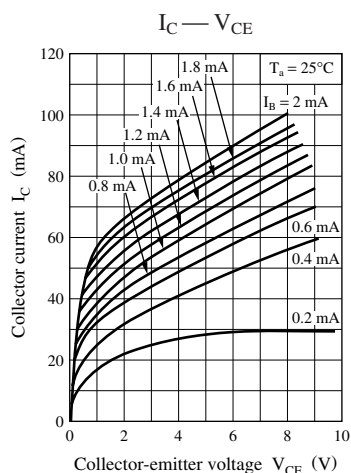
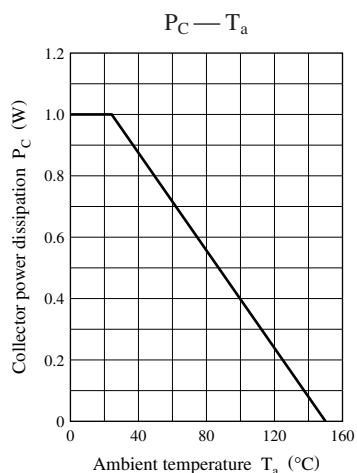
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

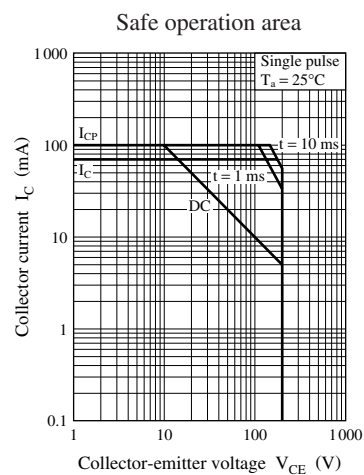
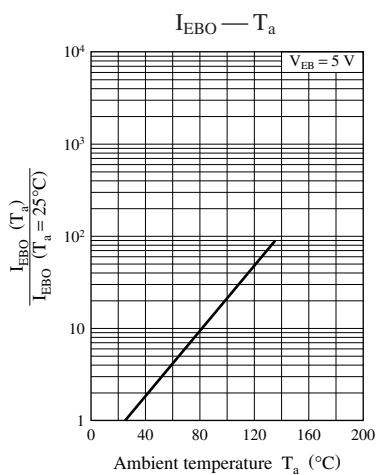
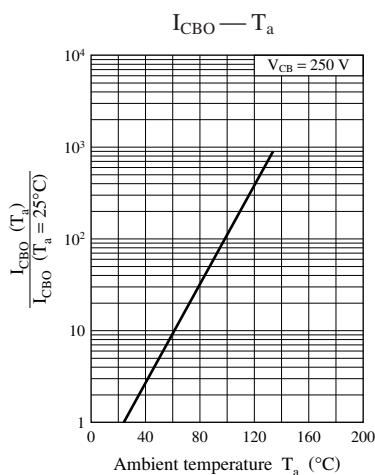
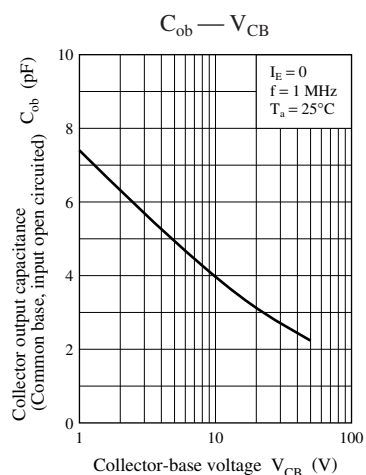
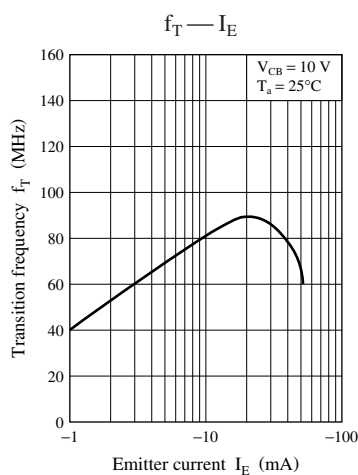
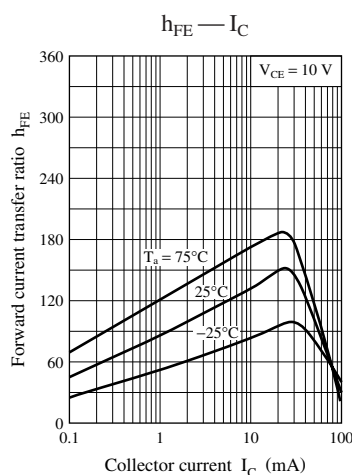
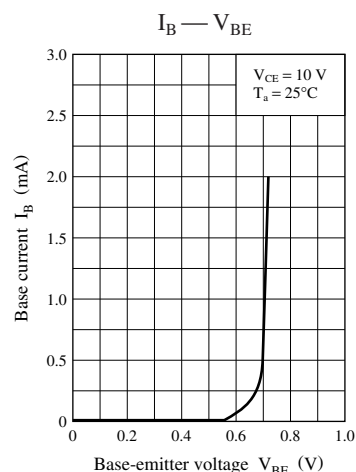
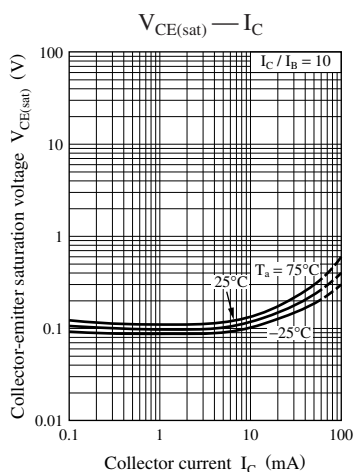
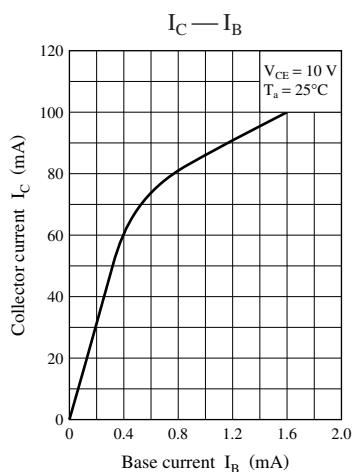
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SC1573	V_{CEO}	$I_C = 100\text{ }\mu\text{A}$, $I_B = 0$	200			V
	2SC1573A			300			
	2SC1573B			400			
Emitter-base voltage (Collector open)	2SC1573	V_{EBO}	$I_E = 1\text{ }\mu\text{A}$, $I_C = 0$	5			V
	2SC1573A			7			
	2SC1573B			7			
Collector-base cut-off current (Emitter open)	2SC1573	I_{CBO}	$V_{\text{CB}} = 12\text{ V}$, $I_E = 0$			2	μA
	2SC1573A						
	2SC1573B		$V_{\text{CB}} = 200\text{ V}$, $I_E = 0$			10	
Forward current transfer ratio	2SC1573	h_{FE} *	$V_{\text{CE}} = 10\text{ V}$, $I_C = 5\text{ mA}$	60		220	—
	2SC1573A			30		220	
	2SC1573B						
Collector-emitter saturation voltage		$V_{\text{CE(sat)}}$	$I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$			1.2	V
Transition frequency		f_T	$V_{\text{CB}} = 10\text{ V}$, $I_E = -10\text{ mA}$, $f = 200\text{ MHz}$	50	80		MHz
Collector output capacitance (Common base, input open circuited)	2SC1573	C_{ob}	$V_{\text{CB}} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$		5	10	pF
	2SC1573A				4	8	
	2SC1573B				4	8	

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification (2SC1573 for ranks Q and R only)

Rank	P	Q	R
h_{FE}	30 to 100	60 to 150	100 to 220





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